

ABSTRACT OF THE DISCLOSURE

A method for fabricating semiconductor devices forms a semiconductor layer containing a positive layer on a mother substrate and then forms a metal layer on the semiconductor layer. After forming the metal layer, the method separates the mother
5 substrate from the semiconductor layer and then removes a desired region of the metal layer from the exposed surface of the semiconductor layer from which the mother substrate has been separated to form a plurality of mutually separated semiconductor devices each containing the semiconductor layer.